

AMENDMENTS TO THE CLAIMS

1. **(Currently amended)** A photoresist composition comprising:
a base material resin component (A) which exhibits changed alkali solubility under the action of acid;
an acid generator component (B) which generates the acid on exposure to radiation; and
at least one nitrogen-containing compound (D) selected from tertiary alkanolamines containing 6 to 12 carbon atoms, wherein
 the base material resin component (A) is a polymer compound comprising:
 an alkali soluble group (i), wherein
 at least one hydrogen atom of a hydroxyl group in the alkali soluble group (i) is protected by an acid dissociable, dissolution inhibiting group (ii) represented by the general formula (1):
 ---CH₂-O-R (1)
 (wherein R represents an organic group containing no more than 20 carbon atoms and at least one hydrophilic group), and
 ~~wherein the polymer compound exhibits changed alkali solubility under the action of acid.~~
2. **(Currently amended)** A ~~polymer compound~~ photoresist composition according to claim 1, wherein the alkali soluble group (i) is selected from the group consisting of an alcoholic hydroxyl group, a phenolic hydroxyl group, and a carboxyl group.
3. **(Currently amended)** A ~~polymer compound~~ photoresist composition according to claim 2, wherein a carbon atom adjacent to the carbon atom connected to the alcoholic hydroxyl group is bonded to at least one fluorine atom.
4. **(Currently amended)** A ~~polymer compound~~ photoresist composition according to claim 1, wherein the hydrophilic group is selected from the group consisting of a carbonyl group, an ester group, an alcoholic hydroxyl group, an ether group, an imino group, and an amino group.
5. **(Canceled)**

6. **(Currently amended)** A resist pattern formation method comprising:
forming a photoresist film on a substrate using the photoresist composition according to claim [[5]] 1;
exposing the photoresist film; and
developing the exposed photoresist film to form a resist pattern.